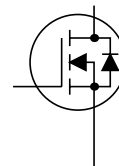
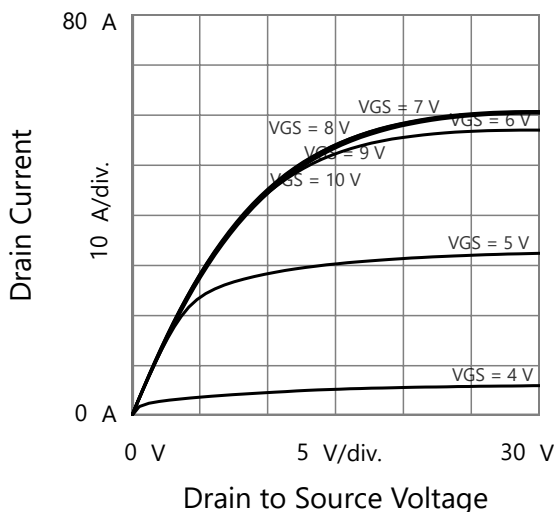


**Part Number:** 3.STW33N60M2  
**Sample ID:** 3B-1  
**Description:** sample  
**Operator:** YM  
**Measurement Instrument:** B1506AH51\_MY59200135

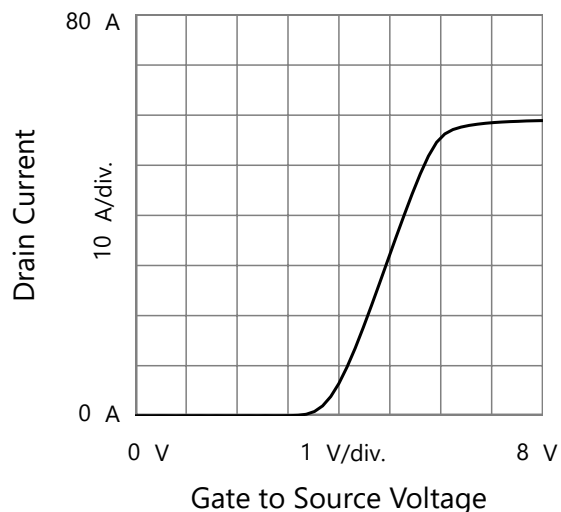


		Maximum Ratings					
Symbol	Parameter	Test Conditions	Value	Unit	Note		
VDSS	Drain to Source Voltage	Tj=-50 °C to 150 °C	600	V			
VGSS	Gate to Source Voltage	Conitnuous	-25 to 25	V			
IDM	Pulsed Drain Current	Tc=25 °C	104	A			
ISM	Pulsed Body Diode Current	Tc=25 °C	104	A			
		Characteristics Parameters					
Symbol	Parameter	Test Conditions	Min.	Act.	Max.	Unit	Note
BVDSS	Drain to Source Breakdown Voltage	VGS=0 V, ID=1 mA	600	647		V	
IDSS	Drain Leakage Current	VDS=600 V, VGS=0 V		2.08 n	1 μ	A	
IGSS	Gate Leakage Current	VGS=25 V, VDS=0 V		666 n	10 μ	A	
IGSS(-)	Gate Leakage Current (-)	VGS=-25 V, VDS=0 V	-10 μ	-735 n		A	
VGS(th)	Gate to Source Threshold Voltage (VDS=VGS)	ID=250 μA	2	2.79	4	V	Typ. 3 V
RDS(on)	Drain to Source On Resistance	VGS=10 V, ID=13 A, PulseWidth=300 μs		150 m	125 m	ohm	Typ. 0.108 ohm
VSD	Body Diode Forward Voltage	VGS=0 V, IS=26 A, PulseWidth=200 μs		986 m	1.6	V	
Rg	Gate Resistance	VGS=0 V, f=1 MHz		5.34		ohm	Typ. 5.2 ohm D-S:short
Ciss	Input Capacitance	VGS=0 V, VDS=100 V, f=100 kHz		1.44 n		F	Typ. 1781 pF
Coss	Output Capacitance	VGS=0 V, VDS=100 V, f=100 kHz		73.2 p		F	Typ. 85 pF
Crss	Reverse Transfer Capacitance	VGS=0 V, VDS=100 V, f=100 kHz		3.01 p		F	2.5 pF
Qg	Total Gate Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=480 V, Id=26 A		36.2 n	1 μ	C	Typ. 45.5 nC
Qgs	Gate to Source Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=480 V, Id=26 A		6.65 n		C	Typ. 9.9 nC
Qgd	Gate to Drain Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=480 V, Id=26 A		15.8 n		C	Typ. 18.5 nC

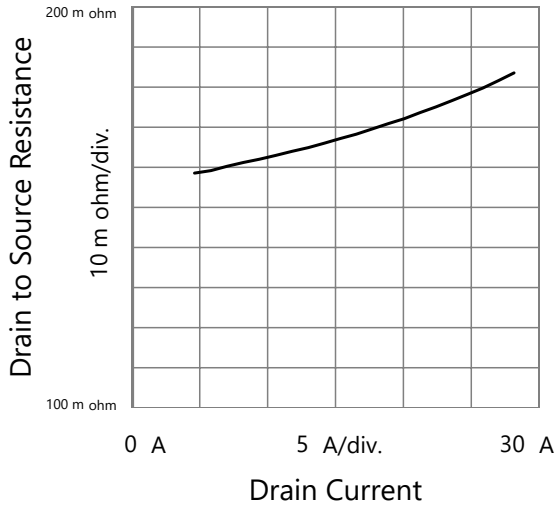
Output Characteristics



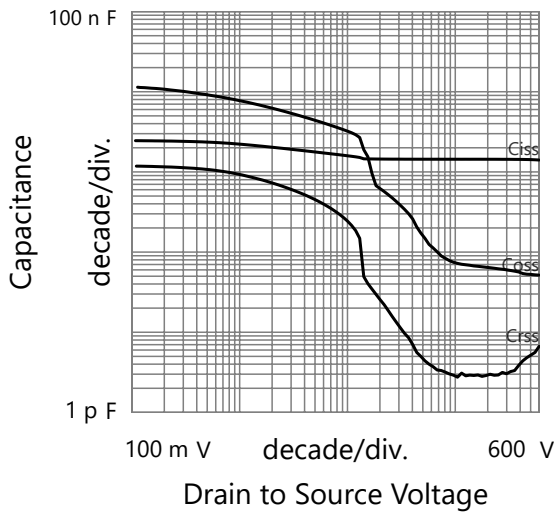
Transfer Characteristics( approximate)



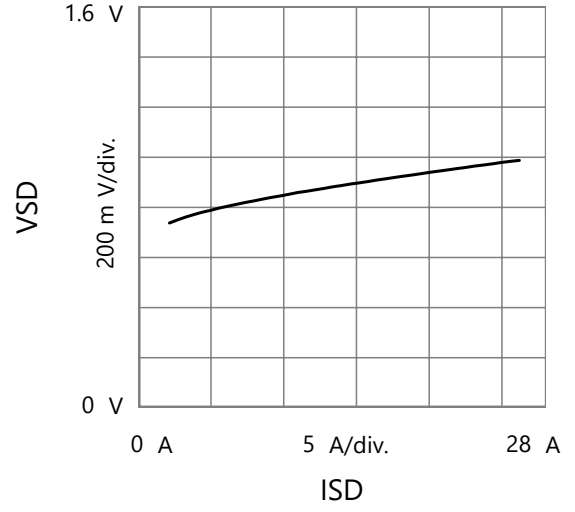
Drain to Source Resistance vs. Drain Current



Capacitances



Body Diode Forward Characteristics



Gate Charge

